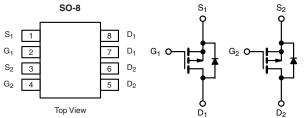


Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.075			
$R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V	0.145			
I _D (A) per leg	- 5			
Configuration	Dual			



P-Channel MOSFET P-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_a and UIS Tested
- AEC-Q101 Qualified^c
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION				
Package	SO-8			
Lead (Pb)-free and Halogen-free	SQ4937EY-T1-GE3			

ABSOLUTE MAXIMUM RATINGS				LINIT
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T _C = 25 °C	1	- 5	
	T _C = 125 °C	- I _D	- 3	
Continuous Source Current (Diode Conduction)		Is	- 3	А
Pulsed Drain Current ^a		I _{DM}	- 20	
Single Pulse Avalanche Current	1 0 1 1	I _{AS}	- 10	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	5	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	D	3.3	14/
	T _C = 125 °C	P_{D}	1.1	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient P	CB Mount ^b	R _{thJA}	110	°C/W		
Junction-to-Foot (Drain)		R_{thJF}	45]		

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							,
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		- 2.0	- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1.0	μА
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	
		$V_{GS} = 0 V$	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 15	-	-	Α
		V _{GS} = - 10 V	I _D = - 3.9 A	-	0.056	0.075	Ω
Drain-Source On-State Resistance ^a	В	V _{GS} = - 10 V	I _D = - 3.9 A, T _J = 125 °C	-	-	0.109	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 3.9 A, T _J = 175 °C	-	-	0.127	
		V _{GS} = - 4.5 V	I _D = - 2 A	-	0.119	0.145	
Forward Transconductanceb	9 _{fs}	V _{DS} =	V _{DS} = - 15 V, I _D = - 3.9 A		6	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	384	480	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V, f} = 1 \text{ MHz}$	-	84	105	pF
Reverse Transfer Capacitance	C _{rss}			-	56	70	1
Total Gate Charge ^c	Qg			-	9.5	15	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -4.9 \text{ A}$	-	1.7	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.3	-	
Gate Resistance	R _g	f = 1 MHz		3.5	-	10.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	6	9	
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 15 Ω $I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	8	12	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	15	23	
Fall Time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Chara	octeristics ^b						
Pulsed Current ^a	I _{SM}				-	- 20	Α
Forward Voltage	V _{SD}	I _F = - 3 A, V _{GS} = 0 V		-	- 0.85	- 1.2	V

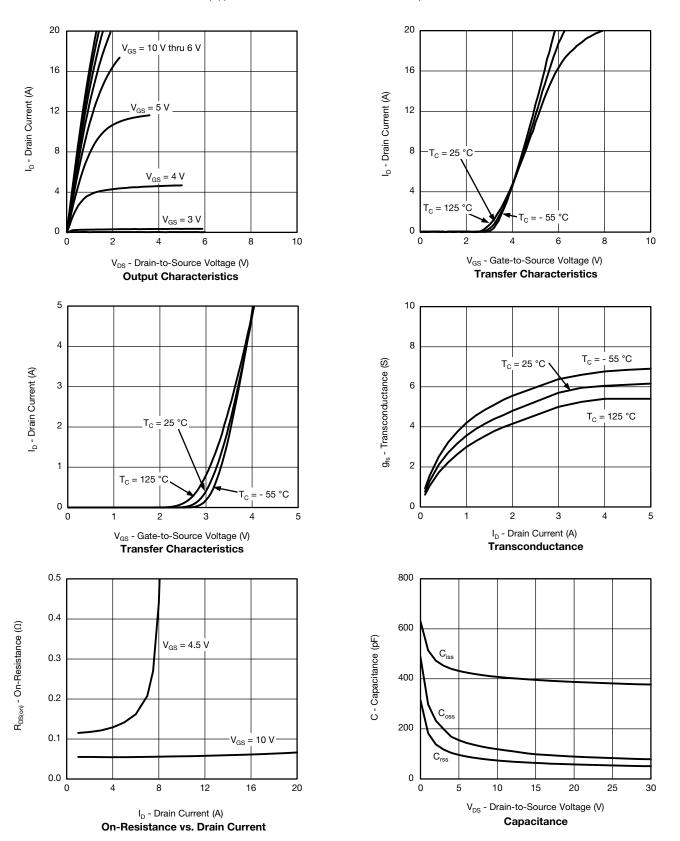
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

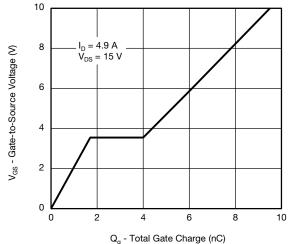


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

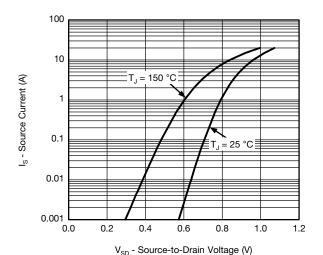




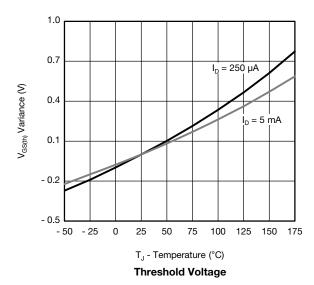
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

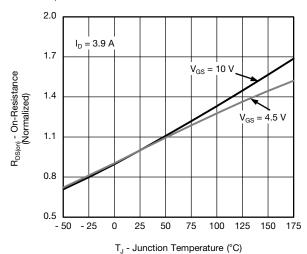


Gate Charge

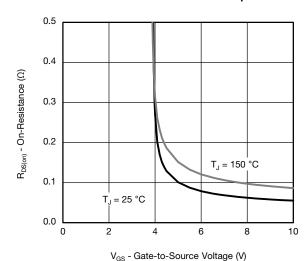


Source Drain Diode Forward Voltage

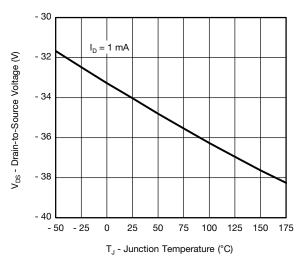




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

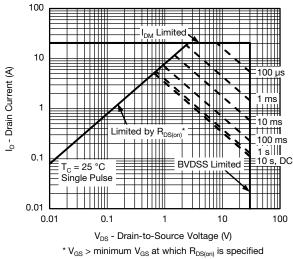


Drain Source Breakdown vs. Junction Temperature



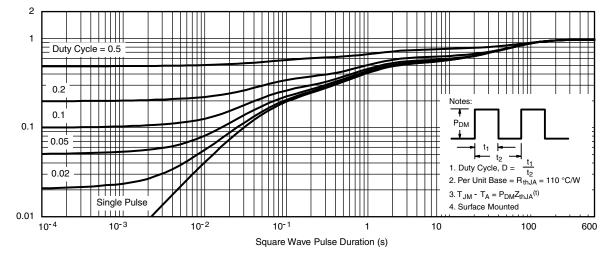
Normalized Effective Transient Thermal Impedance

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



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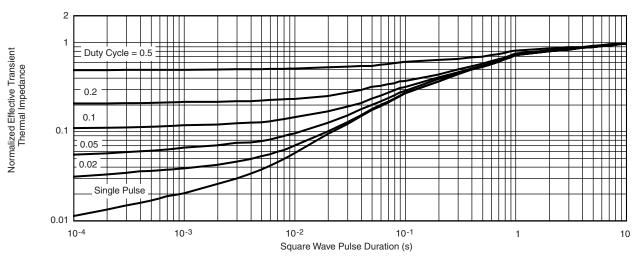
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67043.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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